

SCRs

1.25 Amp, Planar

2N1870A-2N1874A, J

FEATURES

- Available as Either "JAN" or Standard Types
- Operating D.C. Current Range: 5 to 1250mA
- Pulse Currents: to 30A
- Voltage Ratings: to 200V
- Maximum Trigger Current: 0.2mA
- Maximum Trigger Voltage: 0.8V
- All Leads Isolated from Case
- Maximum θ_{J-C} : 20°C/W

DESCRIPTION

These are premium PNPN controlled switches intended for use in applications requiring a high degree of reliability assurance. The JAN types are specified under MIL-S-19500/198, and are included in MIL-STD-701 as recommended types for military usage.

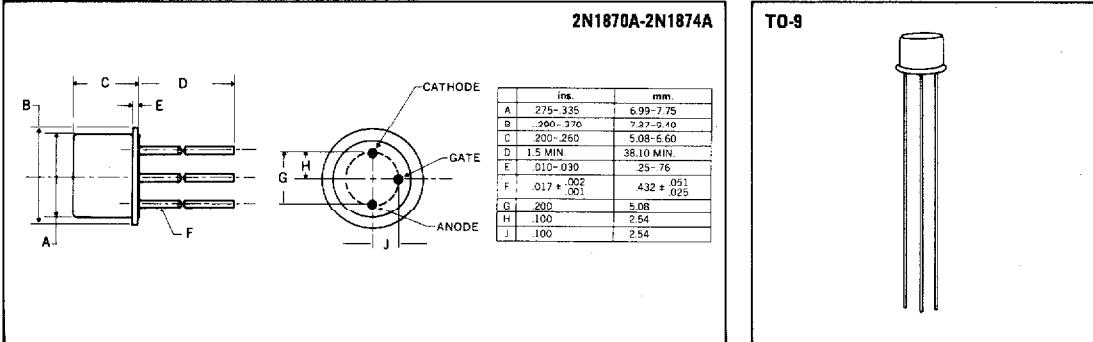
This series is useful in a wide variety of applications including: safety, arming and detonating circuits; timing and programming circuits; protective and warning circuits; driving relays; driving indicator lamps, encoding and decoding circuits; replacing relays, thyratrons, and megamps; servo motor control; pulse generation; plus many others.

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ABSOLUTE MAXIMUM RATINGS

	2N1870A JAN2N1870A	2N1871A JAN2N1871A	2N1872A JAN2N1872A	2N1873A —	2N1874A JAN2N1874A
Repetitive Peak Off-State Voltage, V_{DRM}	30V	60V	100V	150V	200V
Repetitive Peak Reverse Voltage, V_{RRM}	30V	60V	100V	150V	200V
D.C. On-State Current, I_T					
100°C Ambient			250mA		
100°C Case			1.25A		
Repetitive Peak On-State Current, I_{TRM}			up to 30A		
Peak One Cycle Surge (Non-Rep.) On-State Current, I_{ISM}			15A		
Peak Gate Current, I_{GM}			250mA		
Average Gate Current, $I_{C(\Delta V)}$			25mA		
Reverse Gate Voltage, V_{GR}			5V		
Thermal Resistance, Junction to Case, $R\theta_{J-C}$			20°C/W		
Operating and Storage Temperature Range			–65°C to +150°C		

MECHANICAL SPECIFICATIONS



ELECTRICAL SPECIFICATIONS (at 25°C unless noted)†

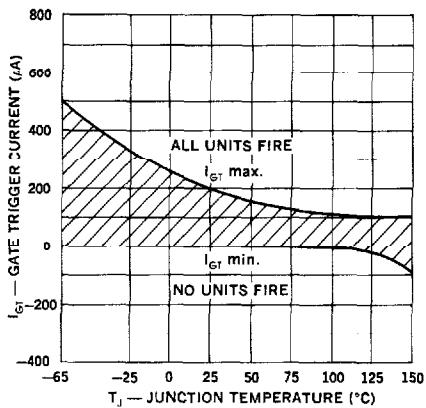
Test	Symbol	Min.	Typical	Max.	Units	Test Conditions
Subgroup 1 (Visual and Mechanical)						
Subgroup 2 (25°C Tests)						
Off-State Current	I_{DRM}	—	0.5	10	μA	$R_{GK} = 1K, V_{DRM} = +$ Rating
Reverse Current	I_{RRM}	—	0.5	10	μA	$R_{GK} = 1K, V_{RRM} = -$ Rating
Gate Trigger Voltage	V_{GT}	0.4	0.55	0.8	V	$R_{GS} = 100$ ohms, $V_D = 5V$
Gate Trigger Current	I_{GT}	—	30	200	μA	$R_{GS} > 10K$ ohms, $V_D = 5V$
On-State Voltage	V_{TM}	—	1.8	2.5	V	$I_{TM} = 2A$ (pulse test)
Off-State Voltage — Critical of Rise	dV_c/dt	100	—	—	V/ μs	Specified test circuit
Reverse Gate Current	I_{GR}	—	0.5	10	μA	$V_{GRM} = 5V$, anode open
Holding Current	I_H	0.3	—	5.0	mA	$I_G = -150\mu A, V_D = 5V$
Subgroup 3 (125°C Tests)						
High Temp. Off-State Current	I_{DRM}	—	15	100	μA	$R_{GK} = 1K, V_{DRM} = +$ Rating
High Temp. Reverse Current	I_{RRM}	—	15	100	μA	$R_{GK} = 1K, V_{RRM} = -$ Rating
High Temp. Gate Non-Trigger Voltage	V_{GD}	0.2	—	—	V	$R_{GS} = 100$ ohms, $V_D = 5V$
High Temp. Holding Current	I_H	0.2	—	—	mA	$I_G = -150\mu A, V_D = 5V$
Subgroup 4 (-65°C Tests)						
Low Temp. Gate Trigger Voltage	V_{GT}	—	—	1.0	V	$R_{GK} = 100$ ohms, $V_D = 5V$
Low Temp. Gate Trigger Current	I_{GT}	—	—	500	μA	$R_{GK} > 10K$ ohms, $V_D = 5V$
Low Temp. Holding Current	I_H	—	—	15	mA	$I_G = -150\mu A, V_D = 5V$

†All values in this table are JEDEC registered.

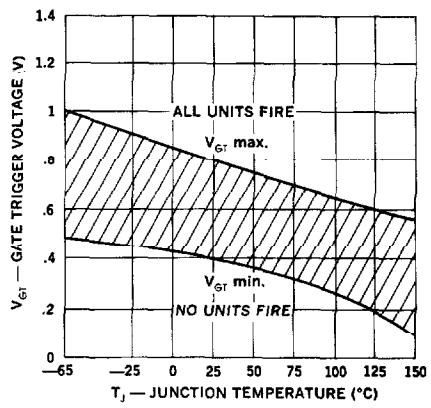
Note: Voltage ratings apply over the full operating temperature range, provided the gate is connected to the cathode through a resistor, 1 K or smaller, or other adequate gate bias is used.

Triggering and Bias Stabilization

1. Gate Trigger Current



2. Gate Trigger Voltage



ELECTRICAL SPECIFICATIONS (at 25°C unless noted)†

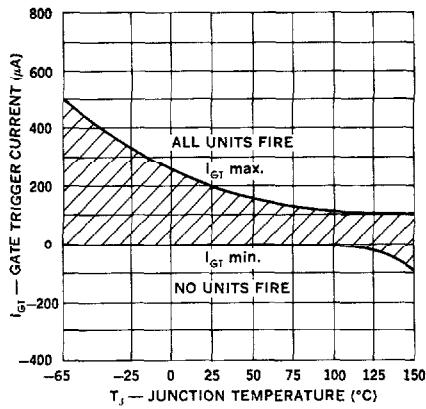
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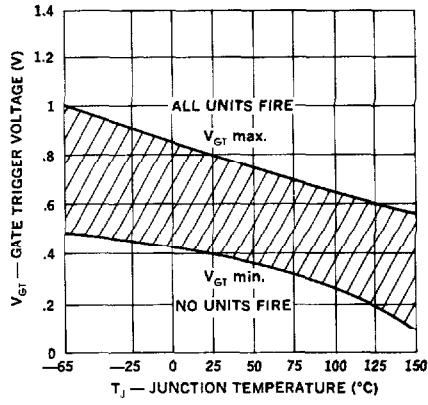
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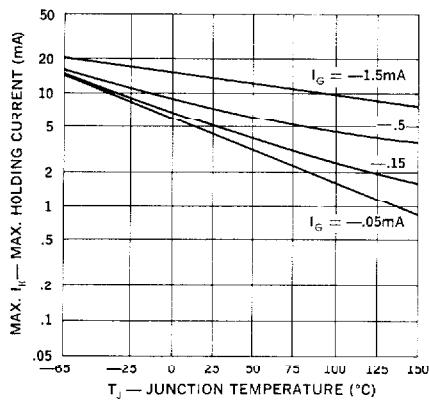
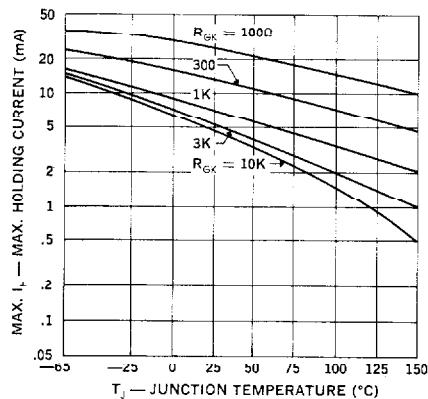
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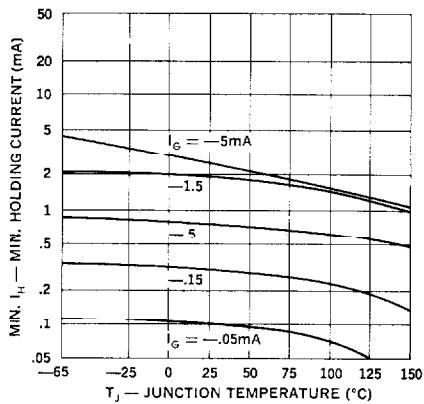
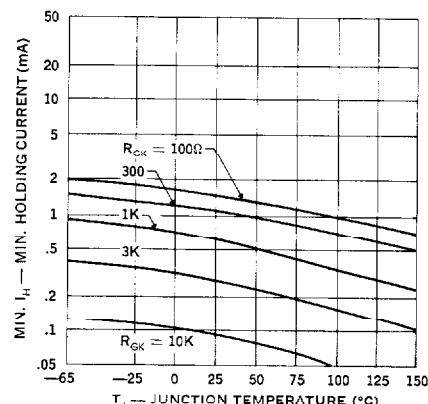


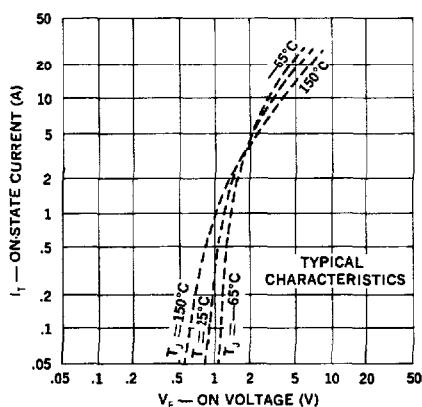
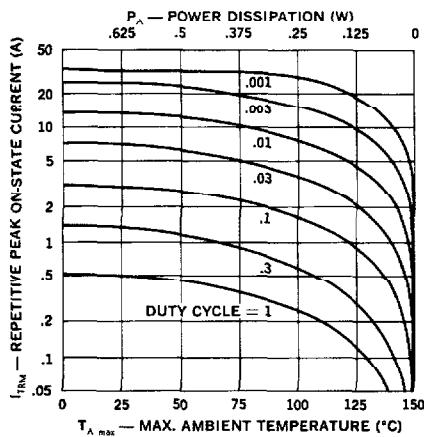
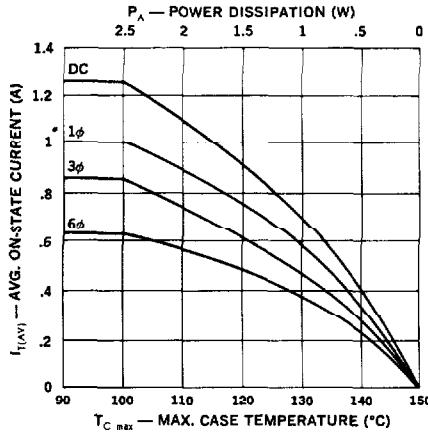
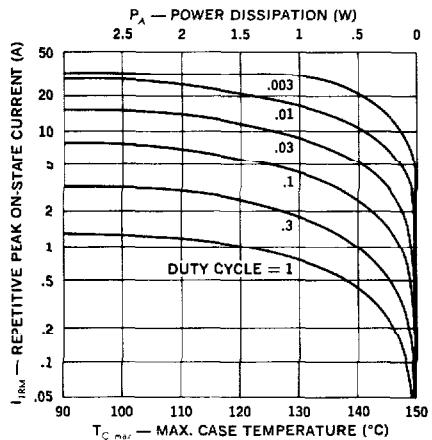
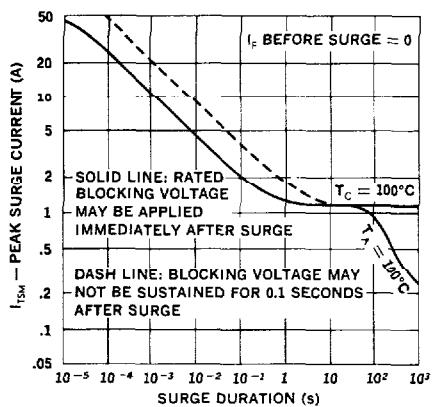
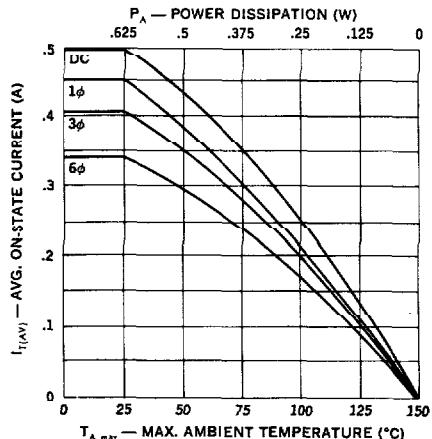
2. Gate Trigger Voltage



Holding Current**1. Max. Holding Current (Current Bias)****2. Max. Holding Current (Resistor Bias)**

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3. Min. Holding Current (Current Bias)**4. Min. Holding Current (Resistor Bias)**

Current Ratings — Thermal Design**1. On-State Current vs. Voltage****3. Peak Current vs. Ambient Temperature****5. Average Current vs. Case Temperature****2. Peak Current vs. Case Temperature****4. Surge Current vs. Time****6. Average Current vs. Ambient Temperature**



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помошь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помошь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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